

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An electroluminescent device, comprising:

first electrodes;

electroluminescent layers disposed over the first electrodes;

a second electrode disposed over the electroluminescent ~~layers;~~ layers and
having a first surface that includes an inorganic oxide; and

a barrier layer ~~in contact with the second electrode,~~ having a second surface
that includes an inorganic compound,

~~at least the surface of the second electrode facing the barrier layer including an~~
~~inorganic oxide, the surface of the second electrode being a separate element from the barrier~~
~~layer, and~~

~~at least the surface of the barrier layer facing the second electrode including an~~
~~inorganic compound, the second surface of the barrier layer being in direct contact with the~~
first surface of the second electrode.
2. (Previously Presented) The electroluminescent device according to claim 1,
the second electrode including indium tin oxide or indium zinc oxide.
3. (Previously Presented) The electroluminescent device according to claim 1,
the second electrode covering side faces and upper faces of the electroluminescent layers.
4. (Previously Presented) The electroluminescent device according to claim 1,
the barrier layer including at least one sublayer composed of a silicon compound.
5. (Previously Presented) The electroluminescent device according to claim 4,
the barrier layer including a sublayer in contact with the second electrode, the sublayer being
composed of silicon oxide.

6. (Previously Presented) The electroluminescent device according to claim 4, the barrier layer including a sublayer in contact with the second electrode, the sublayer being composed of silicon nitride.

7. (Previously Presented) The electroluminescent device according to claim 4, the barrier layer including a sublayer in contact with the second electrode, the sublayer being composed of silicon nitride oxide.

8. (Previously Presented) The electroluminescent device according to claim 1, further comprising:

an insulating layer disposed around the second electrode, the insulating layer being composed of a silicon compound,

the barrier layer extending to the insulating layer.

9. (Previously Presented) The electroluminescent device according to claim 1, further comprising:

a protective layer that covers the barrier layer.

10. (Previously Presented) The electroluminescent device according to claim 9, further comprising:

an adhesive layer disposed between the barrier layer and the protective layer.

11. (Previously Presented) The electroluminescent device according to claim 10, the adhesive layer including a material that is softer than that of the protective layer.

12. (Previously Presented) An electronic apparatus comprising the electroluminescent device according to claim 1.

13. (Withdrawn) A method for manufacturing an electroluminescent device, comprising:

forming a second electrode over electroluminescent layers disposed over a first electrode, the second electrode having a surface being composed of an inorganic oxide; and

forming a barrier layer such that at least one portion of the barrier layer comes into contact with the second electrode, the barrier layer being composed of an inorganic compound.

14. (Withdrawn) The method for manufacturing an electroluminescent device according to claim 13, the second electrode being formed by vapor phase deposition.

15. (Withdrawn) The method for manufacturing an electroluminescent device according to claim 13, the barrier layer being formed by vapor phase deposition.

16. (Withdrawn) The method for manufacturing an electroluminescent device according to claim 13, the second electrode including indium tin oxide or indium zinc oxide.

17. (Withdrawn) The method for manufacturing an electroluminescent device according to claim 13, the barrier layer including a silicon compound.

18. (Withdrawn) The method for manufacturing an electroluminescent device according to claim 17, the barrier layer having a sublayer in contact with the second electrode, the sublayer being composed of silicon oxide.

19. (Withdrawn) The method for manufacturing an electroluminescent device according to claim 17, the barrier layer having a sublayer in contact with the second electrode, the sublayer being composed of silicon nitride.

20. (Withdrawn) The method for manufacturing an electroluminescent device according to claim 17, the barrier layer having a sublayer in contact with the second electrode, the sublayer being composed of silicon nitride oxide.

21. (Withdrawn) The method for manufacturing an electroluminescent device according to claim 13, the barrier layer extending to an insulating layer disposed around the second electrode, the insulating layer being composed of a silicon compound.

22. (New) An electroluminescent device comprising:
- first electrodes;
 - electroluminescent layers being disposed over the first electrodes;
 - a second electrode being disposed over the electroluminescent layers and including an inorganic oxide; and
 - a barrier layer including an inorganic compound,
 - the inorganic oxide of the second electrode directly contacting the inorganic compound of the barrier layer.
23. (New) An electroluminescent device comprising:
- first electrodes;
 - electroluminescent layers disposed over the first electrodes;
 - a second electrode being disposed over the electroluminescent layers and including an inorganic oxide; and
 - a barrier layer being disposed on the second electrode and including silicon compound,
 - the inorganic oxide of the second electrode directly contacting the silicon compound of the barrier layer.
24. (New) An electroluminescent device comprising:
- anodes;
 - electroluminescent layers disposed over the anodes;
 - a cathode being disposed over the electroluminescent layers and including an inorganic conductive oxide; and
 - a barrier layer including an inorganic compound,
 - the inorganic oxide of the cathode directly contacting the inorganic compound of the barrier layer.